



### **AUIRFR8405TRL Information**



For Reference Only

**Part Number** AUIRFR8405TRL **Manufacturer** Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 40V 100A DPAK

Package TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

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## **AUIRFR8405TRL Specifications**

Manufacturer Part NumberAUIRFR8405TRLManufacturerInfineon TechnologiesCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-252-3, DPak (2 Leads + Tab), SC-63SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C100A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.9V @ 100μAGate Charge (Qg) (Max) @ Vgs155nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5171pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)163W (Tc)		
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Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  155nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  5171pF @ 25V  Vgs (Max)  FET Feature  Power Dissipation (Max)  40V  100A (Tc)  100V  10V  519V  100µA  155nC @ 10V  155nC @ 10V  163W (Tc)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C       100A (Tc)         Drive Voltage (Max Rds On, Min Rds On)       10V         Vgs(th) (Max) @ Id       3.9V @ 100μA         Gate Charge (Qg) (Max) @ Vgs       155nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       5171pF @ 25V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       163W (Tc)	Technology	MOSFET (Metal Oxide)
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Power Dissipation (Max) 163W (Tc)	Vgs (Max)	±20V
	FET Feature	-
	Power Dissipation (Max)	163W (Tc)
Rds On (Max) @ Id, Vgs 1.98 mOhm @ 90A, 10V	Rds On (Max) @ Id, Vgs	1.98 mOhm @ 90A, 10V
Operating Temperature $-55^{\circ}\text{C} \sim 175^{\circ}\text{C} \text{ (TJ)}$	Operating Temperature	-55°C ~ 175°C (TJ)
Mounting Type Surface Mount	Mounting Type	Surface Mount
Supplier Device Package D-Pak	Supplier Device Package	D-Pak
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
Report errors?		Report errors?

### **AUIRFR8405TRL Guarantees**



### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### **AUIRFR8405TRL Payment Methods**



















## **AUIRFR8405TRL Shipping Methods**













If you have any question about AUIRFR8405TRL, please do not hesitate to contact us!

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